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November 2014

FGA20S125P 1250 V, 20 A Shorted-anode IGBT

Features

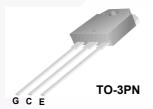
- · High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.0 V @ I_C = 20 A
- · High Input Impedance
- RoHS Compliant

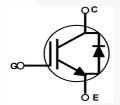
Applications

· Induction Heating, Microwave oven

General Description

Using advanced field stop trench and shorted anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche capability. This device is designed for induction heating and microwave oven.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	nbol Description		FGA20S125P_SN00336	Unit
V _{CES}	Collector to Emitter Voltage		1250	V
V _{GES}	Gate to Emitter Voltage		±25	V
I _C	Collector Current	$^{\circ}$ T _C = 25 $^{\circ}$ C	40	А
	Collector Current	@ T _C = 100°C	20	А
I _{CM (1)}	Pulsed Collector Current		60	A
l _F	Diode Continuous Forward Current	@ T _C = 25°C	40	A
l _F	Diode Continuous Forward Current	@ T _C = 100°C	20	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	250	W
	Maximum Power Dissipation	@ T _C = 100°C	125	W
T _J	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit	
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case		0.6	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		40	°C/W	

Notes: 1: Limited by Tjmax

Package Marking and Ordering Information

Device Marking	Device	Package	kage Reel Size Tape Width		Quantity	
FGA20S125P	FGA20S125P SN00336	TO-3PN	-	-	30	

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	1250	-	-	V
ΔBV _{CES} ΔΤ _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	-	1.2	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = 1250, V _{GE} = 0V	-	-	1	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	±500	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I _C = 20mA, V _{CE} = V _{GE}	4.5	6.0	7.5	V
OL(III)		I _C = 20A, V _{GE} = 15V T _C = 25°C		2.0	2.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 20A, V _{GE} = 15V, T _C = 125°C	-	2.22	-	V
		I _C = 20A, V _{GE} = 15V, T _C = 175°C	-	2.44	-	V
V _{FM} Diode	Diode Forward Voltage	I _F = 20A, T _C = 25°C	-	1.75	2.4	٧
	Blode Forward Vollage	I _F = 20A, T _C = 175°C	-	2.22	-	V
Dynamic C	haracteristics					
C _{ies}	Input Capacitance	\\ - 30\\\\ - 0\\	-	1360	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$ f = 1MHz	-	40	-	pF
C _{res}	Reverse Transfer Capacitance		-	26	-	pF
Switching	Characcteristics					
t _{d(on)}	Turn-On Delay Time		-	10	-	ns
t _r	Rise Time		-	260	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 600V, I _C = 20A,	-	400	-	ns
t _f	Fall Time	$R_G = 10\Omega$, $V_{GE} = 15V$,	-	100	- 7	ns
E _{on}	Turn-On Switching Loss	Resistive Load, T _C = 25°C	-	0.74	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.50	-	mJ
E _{ts}	Total Switching Loss		-	1.24	-	mJ
t _{d(on)}	Turn-On Delay Time		-	11	- /	ns
t _r	Rise Time		-	320	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 600V, I _C = 20A,	-	420	-	ns
t _f	Fall Time	$R_G = 10\Omega, V_{GE} = 15V,$	_	250	-	ns
E _{on}	Turn-On Switching Loss	Resistive Load, T _C = 175°C	-	0.94	-	mJ
E _{off}	Turn-Off Switching Loss		-	1.23	-	mJ
E _{ts}	Total Switching Loss		-	2.17	-	mJ
$\overline{Q_g}$	Total Gate Charge		-	153	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600V, I_{C} = 20A,$	-	12	-	nC
Q _{gc}	Gate to Collector Charge	V _{GE} = 15V	_	98		nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

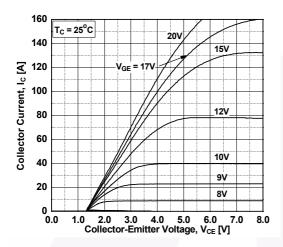


Figure 3. Typical Saturation Voltage Characteritics

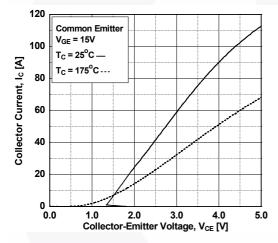


Figure 5. Saturation Voltage vs. Case

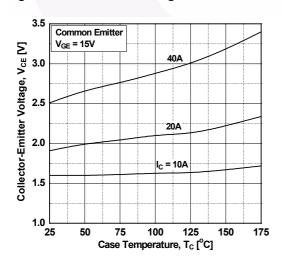


Figure 2. Typical Saturation Voltage Characteristics

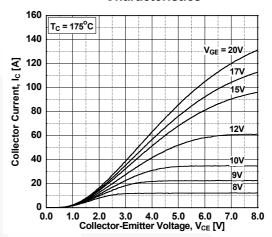


Figure 4. Transfer Characteristics

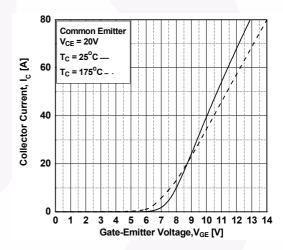
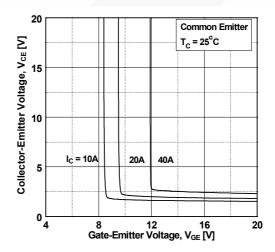


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. Vge

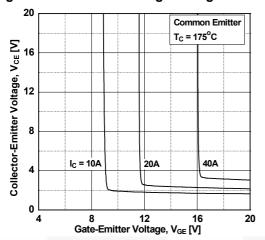


Figure 9. Gate Charge Characteristics

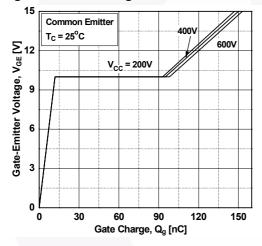


Figure 11. Turn-On Characteristics vs Gate Resistance

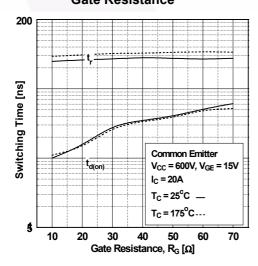


Figure 8. Capacitance Characteristics

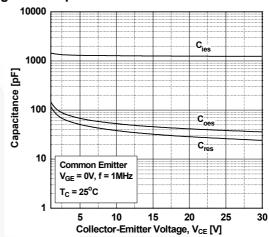


Figure 10. SOA Characteristics

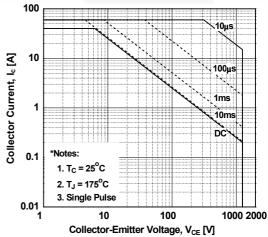
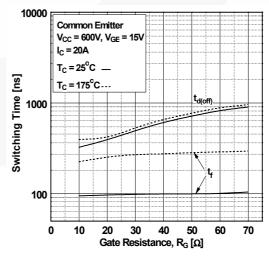


Figure 12. Turn-off Characteristics vs.
Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics VS. Collector Current

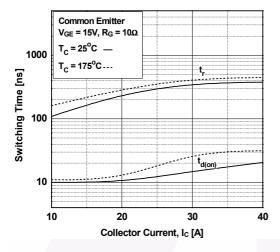


Figure 14.Turn-off Characteristics VS.
Collector Current

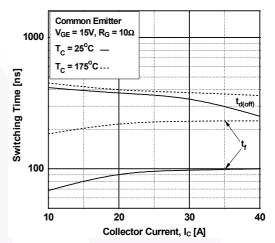


Figure 15. Switching Loss VS. Gate Resistance

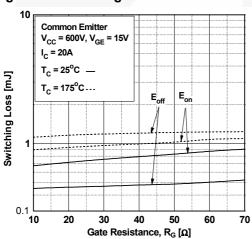


Figure 16. Switching Loss VS. Collector Current

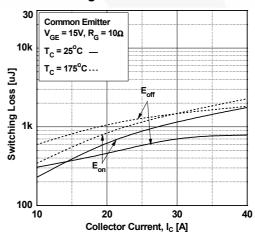


Figure 17. Turn off Switching SOA Characteristics

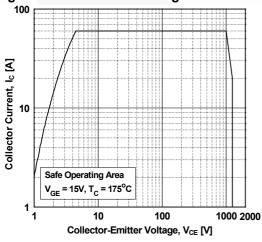


Figure 18. Forward Characteristics

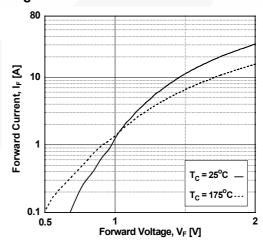
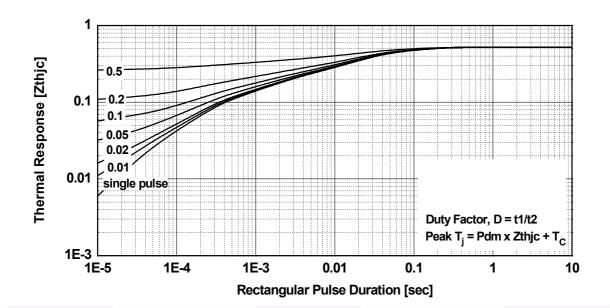


Figure 19. Transient Thermal Impedance of IGBT



Mechanical Dimensions 5.00 4.60 13.80 13.40 Ø 3.30 3.10 1.65 16.20 5.20 1.45 15.40 4.80 (R0.50) 16.96 20.10 18.90 16.56 19.70 18.50 3 3.70 (1.85) 3.30 20.30 2.20 2.90 19.70 1.80 1.90 3.20 2.80 1.20 0.80 $| \oplus | \phi$ 0.55 (M)0.75 0.55 5.45 5.45 NOTES: UNLESS OTHERWISE SPECIFIED A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSION AND TOLERANCING PER (R0.50) ASME14.5-2009. ASME 14.5-2009. D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. E) DRAWING FILE NAME: TO3PN03AREV1. F) FAIRCHILD SEMICONDUCTOR.

Figure 20. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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